

Title (en)

TWO-STEP METHOD FOR JOINING A SEMICONDUCTOR TO A SUBSTRATE WITH CONNECTING MATERIAL BASED ON SILVER

Title (de)

ZWEISTUFIGES VERFAHREN ZUM FÜGEN EINES HALBLEITERS AUF EIN SUBSTRAT MIT VERBINDUNGSMATERIAL AUF SILBERBASIS

Title (fr)

PROCÉDÉ À DEUX NIVEAUX POUR ASSEMBLER UN SEMI-CONDUCTEUR SUR UN SUBSTRAT AVEC UN MATÉRIAU DE L'IAISON À BASE D'ARGENT

Publication

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Application

EP 13715652 A 20130402

Priority

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Abstract (en)

[origin: WO2013167321A1] The invention relates to a method for joining a semiconductor (20) to a substrate (10), comprising the following steps: . applying a first paste layer (1) of a sintering paste to the substrate; . heating and compressing the first paste layer to form a first sintered layer; . applying a second paste layer (2) of a sintering paste to the first sintered layer and arranging a semiconductor (20) on the second paste layer; . heating and compressing the second paste layer (2) to form a second sintered layer. The invention further relates to a semiconductor component produced by means of the method.

IPC 8 full level

H01L 21/60 (2006.01)

CPC (source: EP US)

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Citation (search report)

See references of WO 2013167321A1

Citation (examination)

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- EP 2425920 A1 20120307 - HERAEUS MATERIALS TECH GMBH [DE]
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